Markku A Sopanen

List of Publications by Year
in descending order

53 papers	1,098 citations	566801 15 h-index	414034 32 g-index
53 all docs	53 docs citations	53 times ranked	976 citing authors

#	Article	IF	Citations
1	Metalorganic vapor phase epitaxy of wurtzite InP nanowires on GaN. Applied Physics Letters, 2020, 116, 093101.	1.5	2
2	Nonlinear plasmonic behavior of nanohole arrays in thin gold films for imaging lipids. Applied Physics Letters, 2018, 112, .	1.5	7
3	Grass-like Alumina with Low Refractive Index for Scalable, Broadband, Omnidirectional Antireflection Coatings on Glass Using Atomic Layer Deposition. ACS Applied Materials & Interfaces, 2017, 9, 15038-15043.	4.0	38
4	Atomic layer etching of gallium nitride (0001). Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2017, 35, .	0.9	37
5	Fluorescence-enhancing plasmonic silver nanostructures using azopolymer lithography. RSC Advances, 2016, 6, 48129-48136.	1.7	9
6	A technique for large-area position-controlled growth of GaAs nanowire arrays. Nanotechnology, 2016, 27, 135601.	1.3	9
7	Optical degradation and defect activation in MOVPE grown near surface InGaN quantum wells under low energy electron beam irradiation. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 806-809.	0.8	0
8	Photocatalytic degradation of dyes by CdS microspheres under near UV and blue LED radiation. Separation and Purification Technology, 2013, 120, 206-214.	3.9	72
9	Recombination lifetime in InGaN/GaN based light emitting diodes at low current densities by differential carrier lifetime analysis. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 327-331.	0.8	10
10	Analysis of Dislocations Generated during Metalâ€"Organic Vapor Phase Epitaxy of GaN on Patterned Templates. Japanese Journal of Applied Physics, 2013, 52, 01AF01.	0.8	2
11	Band-Edge Luminescence Degradation by Low Energy Electron Beam Irradiation in GaN Grown by Metalâ€"Organic Vapor Phase Epitaxy in H2and N2Ambients. Japanese Journal of Applied Physics, 2013, 52, 11NH04.	0.8	0
12	Thermally assisted recovery of low energy electron beam irradiation induced optical degradation of GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 461-463.	0.8	3
13	High Quality GaAs Nanowires Grown on Glass Substrates. Nano Letters, 2012, 12, 1912-1918.	4.5	70
14	Low energy electron beam induced damage on gallium nitride based materials. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1563-1565.	0.8	7
15	Growth and characterization of GaP layers on silicon substrates by metalâ€organic vapour phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1607-1609.	0.8	11
16	Effect of atomic-layer-deposited AlN on near-surface InGaAs/GaAs structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1560-1562.	0.8	1
17	Synchrotron radiation Xâ€ray topography and Xâ€ray diffraction of homoepitaxial GaN grown on ammonothermal GaN. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 1630-1632.	0.8	7
18	Temperature Dependence of Current-Voltage Characteristics of Auâˆ•Ga[sub 0.51]In[sub 0.49]P Schottky Barrier Diodes. AIP Conference Proceedings, 2011, , .	0.3	10

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19	Temperature Dependence Of Current-Voltage Characteristics Of Auâˆ•p-GaAsN Schottky Barrier Diodes, With Small N Content. , 2011, , .		1
20	Nonlinear dynamics of non-equilibrium holes in p-type modulation-doped GaInNAs/GaAs quantum wells. Nanoscale Research Letters, 2011, 6, 191.	3.1	2
21	Inhomogeneous Barrier Height Analysis of (Ni/Au)â€“InAlGaN/GaN Schottky Barrier Diode. Japanese Journal of Applied Physics, 2011, 50, 030201.	0.8	10
22	Recent progress towards acoustically mediated carrier injection into individual nanostructures for single photon generation. Proceedings of SPIE, 2010, , .	0.8	1
23	Defect studies with positrons: What could we learn on III-nitride heterostructures?. Journal of Physics: Conference Series, 2010, 225, 012057.	0.3	1
24	Forward Bias Capacitance-Voltage Measurements on Semiconductors Using Co-Planar Ohmic and Schottky Contacts in a Cylindrical Geometry. Journal of Nano Research, 2010, 12, 45-54.	0.8	2
25	GaAs Nanowire and Crystallite Growth on Amorphous Substrate from Metalorganic Precursors. Japanese Journal of Applied Physics, 2010, 49, 020213.	0.8	2
26	InGaN-based 405 nm near-ultraviolet light emitting diodes on pillar patterned sapphire substrates. CrystEngComm, 2010, 12, 3152.	1.3	13
27	Tunneling Explanation for the Temperature Dependence of Currentâ€“Voltage Characteristics of Pt/InN Schottky Barrier Diodes. Japanese Journal of Applied Physics, 2009, 48, 070201.	0.8	8
28	Carrier Dynamics in Strain Induced Quantum Dots Modeled by Rate Equations and Gaussian Excitation Beam Distribution. Japanese Journal of Applied Physics, 2008, 47, 5499-5502.	0.8	0
29	Metal Contacts on InN: Proposal for Schottky Contact. Japanese Journal of Applied Physics, 2006, 45, 36-39.	0.8	22
30	Evolution of Self-Assembled InAs/InP Islands into Quantum Rings. Japanese Journal of Applied Physics, 2005, 44, L1323-L1325.	0.8	3
31	Highly Tunable Emission from Strain-Induced InGaAsP/InP Quantum Dots. Japanese Journal of Applied Physics, 2005, 44, L976-L978.	0.8	2
32	InGaAs/InP Quantum Dots Induced by Self-Organized InAs Stressor-Islands. Japanese Journal of Applied Physics, 2005, 44, L518-L520.	0.8	8
33	Transformation of Self-Assembled InAs/InP Quantum Dots into Quantum Rings without Capping. Nano Letters, 2005, 5, 1541-1543.	4.5	36
34	Longitudinal Stark Effect in Parabolic Quantum Dots. Japanese Journal of Applied Physics, 2001, 40, 2002-2005.	0.8	6
35	Effect Of Inp Passivation On Carrier Recombination in InxGa1-xAs/GaAs Surface Quantum Wells. Japanese Journal of Applied Physics, 1999, 38, 1133-1134.	0.8	6
36	Tailoring of Energy Levels in Strain-Induced Quantum Dots. Japanese Journal of Applied Physics, 1999, 38, 1081-1084.	0.8	8

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37	Fabrication of GaInAs quantum disks using selfâ€organized InP islands as a mask in wet chemical etching. Applied Physics Letters, 1996, 69, 4029-4031.	1.5	3
38	Fabrication and photoluminescence of quantum dots induced by strain of self-organized stressors. Solid-State Electronics, 1996, 40, 601-604.	0.8	15
39	Metalorganic vapor phase epitaxial growth of AlGaSb and AlGaAsSb using all-organometallic sources. Journal of Crystal Growth, 1996, 169, 417-423.	0.7	17
40	Red luminescence from strainâ€induced GaInP quantum dots. Applied Physics Letters, 1996, 69, 3393-3395.	1.5	17
41	Enhanced optical properties of in situ passivated nearâ€surface AlxGa1â^'xAs/GaAs quantum wells. Applied Physics Letters, 1996, 68, 2216-2218.	1.5	32
42	Zeeman Effect in Parabolic Quantum Dots. Physical Review Letters, 1996, 77, 342-345.	2.9	99
43	Recombination processes in strain-induced InGaAs quantum dots. Nuovo Cimento Della Societa Italiana Di Fisica D - Condensed Matter, Atomic, Molecular and Chemical Physics, Biophysics, 1995, 17, 1699-1703.	0.4	7
44	Growth of high-quality GaSb by metalorganic vapor phase epitaxy. Journal of Electronic Materials, 1995, 24, 1691-1696.	1.0	20
45	Luminescence from excited states in strain-inducedInxGa1â^'xAs quantum dots. Physical Review B, 1995, 51, 13868-13871.	1.1	174
46	Strainâ€induced quantum dots by selfâ€organized stressors. Applied Physics Letters, 1995, 66, 2364-2366.	1.5	88
47	Selfâ€organized InP islands on (100) GaAs by metalorganic vapor phase epitaxy. Applied Physics Letters, 1995, 67, 3768-3770.	1.5	70
48	Selective growth of InGaAs on nanoscale InP islands. Applied Physics Letters, 1994, 65, 1662-1664.	1.5	93
49	Growth of GaInAsSb using tertiarybutylarsine as arsenic source. Journal of Crystal Growth, 1994, 145, 492-497.	0.7	30
50	Photoluminescence of buried InGaAs grown on nanoscale InP islands by MOVPE. Journal of Crystal Growth, 1994, 145, 988-989.	0.7	3
51	Fabrication of nanostructures using MBE and MOVPE. Physica Scripta, 1994, T54, 241-243.	1.2	1
52	Praseodymium Dioxide Doping of In1â^'xGaxAsyP1â^'y Epilayer Grown with Liquid Phase Epitaxy. Materials Research Society Symposia Proceedings, 1993, 301, 27.	0.1	2
53	Optical properties of self-organized InGaAs/InP dots. , 0, , .		1